Correction to: Comparison from Simulated Al_{0.3}Ga_{0.7}As/GaAs/Ge and Al_{0.3}Ga_{0.7}As/GaAs/Si/Ge to Experimental InGaP/GaAs/InGaAsSb/Ge for Optimized Utilization of the Solar Spectrum

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Figures 6(a)(b)(c) and Figure 7(a)(b) did not credit the original source. These figures have been reproduced from *Nature Materials* (2014) 13, 593–598, with permission.

The additional figures below have been included as Fig. 8(a) and (b).

The original article can be found online at <https://doi.org/10.1007/s11664-020-08722-6>.

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Fig. 8 (a) SEM images (cross-sectional view) of a 3J/trilayer/Ge cell, showing the aligned metal contact lines and the interfacial trilayer. (b) XRD of TiO_2 film for Trilayer. (a) Presents SEM images (cross-sectional view) of a mechanically stacked 3J/trilayer/Ge cell, showing the aligned metal contact lines and the interfacial trilayer. The XRD patterns of SiO_2 and TiO_2 for trilayer film have been obtained. Since

SiO_2 is amorphous, only XRD of TiO_2 film has been displayed as (b). The three broad characteristic peaks at $2\theta = 25.2^\circ$, 37.8° , 48.1° of anatase phase have been observed, which were well indexed to (1 0 1), (0 0 4) and (2 0 0) plane diffraction of anatase TiO_2 . Therefore, it can be considered that TiO_2 for $\text{TiO}_2/\text{SiO}_2/\text{TiO}_2$ trilayer film is anatase TiO_2 .